

Characteristics

Table 1. Absolute ratings (limiting values per diode at 25 °C, unless otherwise specified)

Symbol	Parameter	Value	Unit		
V_{RRM}	Repetitive peak reverse voltage			170	V
I _{F(RMS)}	Forward rms current				Α
I _{F(AV)}	T _c :		Per diode	30	
	Average forward current, δ = 0.5, square wave	T _c = 145 °C	Per device	60	Α
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms sin	usoidal	500	Α
P _{ARM}	Repetitive peak avalanche power	t _p = 10 μs, T _j =	t _p = 10 μs, T _j = 125 °C		
T _{stg}	Storage temperature range			-65 to +175	°C
Tj	Maximum operating junction temperature (1)			+175	°C

^{1.} $(dP_{tot}/dT_j) < (1/R_{th(j-a)})$ condition to avoid thermal runaway for a diode on its own heatsink.

Table 2. Thermal resistance parameters

Symbol	Parameter		Typ. value	Unit
D.,	Junction to case	Per diode	0.9	°C/W
R _{th(j-c)}		Total	0.6	C/VV
R _{th(c)}	Coupling		0.3	°C/W

When the diodes 1 and 2 are used simultaneously: $\Delta T_{j \text{ (diode1)}} = P_{\text{(diode1)}} \times R_{\text{th(j-c)}}$ (per diode) + $P_{\text{(diode2)}} \times R_{\text{th(c)}}$

For more information, please refer to the following application note:

AN5088: Rectifiers thermal management, handling and mounting recommendations

Table 3. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾	Reverse leakage current	T _j = 25 °C	$V_R = V_{RRM}$	-		60	μA
'R '		T _j = 125 °C		-	16	60	mA
		T _j = 25 °C	L = 20 A	-		0.84	
V _F ⁽²⁾		0.63	0.67	V			
VF (=)	Forward voltage drop		0.92				
		T _j = 125 °C	IF - 00 X	-	0.76	0.80	

- 1. Pulse test: $t_p = 5$ ms, $\delta < 2\%$
- 2. Pulse test: t_p =380 μ s, δ < 2%

To evaluate the conduction losses, use the following equation: P = 0.54 x $I_{F(AV)}$ + 0.0043 x I_{F} 2 (RMS)

For more information, please refer to the following application notes related to the power losses:

- AN604: Calculation of conduction losses in a power rectifier
- AN4021: Calculation of reverse losses on a power diode

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1.1 Characteristics (curves)

Figure 1. Average forward power dissipation versus average forward current (per diode)

P_{F(AV)}(W)

5=0.05

5=0.1

5=0.2

5=1.0

Figure 2. Average forward current versus ambient temperature (δ = 0.5, per diode) $I_{F(AV)}(A)$ $R_{th(j-a)}=R_{th(j-c)}$

Figure 3. Normalized avalanche power derating versus pulse duration (T_i= 125 °C)

 $I_{F(AV)}(A)$

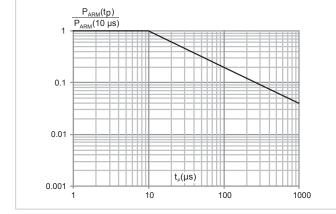
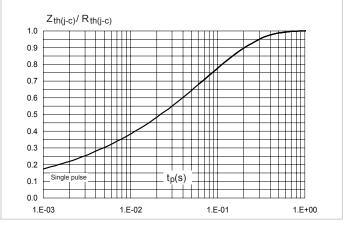


Figure 4. Relative variation of thermal impedance junction to case versus pulse duration



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Figure 5. Reverse leakage current versus reverse voltage applied (typical values, per diode)

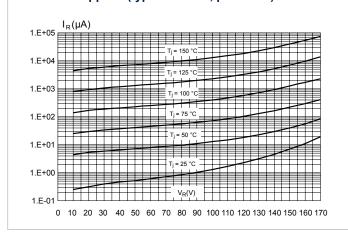


Figure 6. Junction capacitance versus reverse voltage applied (typical values, per diode)

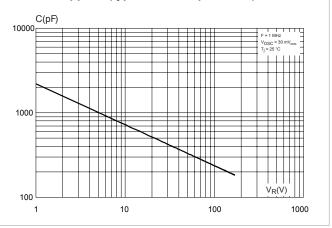


Figure 7. Forward voltage drop versus forward current (per diode, low level)

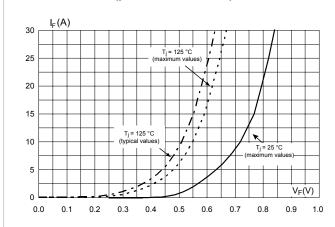
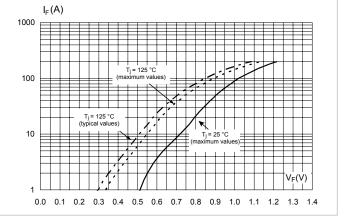


Figure 8. Forward voltage drop versus forward current (per diode, high level)



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Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

2.1 TO-247 package_information

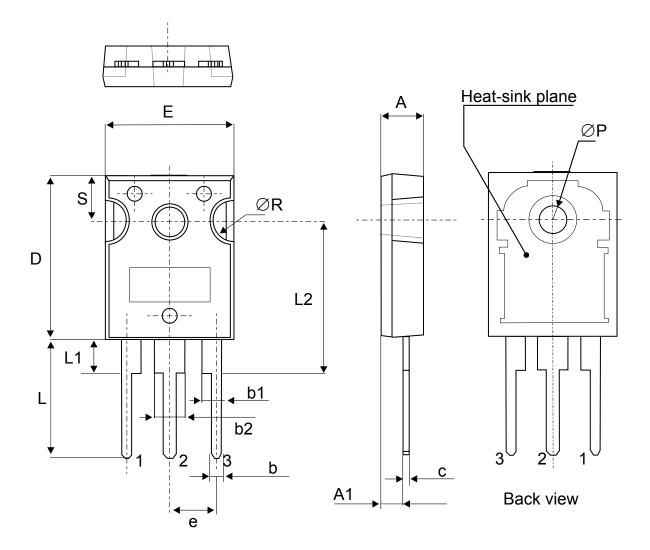
• Epoxy meets UL94, V0

Cooling method: by conduction (C)

Recommended torque value: 0.8 N·m

Maximum torque value: 1.0 N·m

Figure 9. TO-247 package outline



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Table 4. TO-247 package mechanical data

			Dime	nsions			
Ref.	Millimeters			Inches (for reference only)			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
Α	4.85		5.15	0.191		0.203	
A1	2.20		2.60	0.086		0.102	
b	1.00		1.40	0.039		0.055	
b1	2.00		2.40	0.078		0.094	
b2	3.00		3.40	0.118		0.133	
С	0.40		0.80	0.015		0.031	
D	19.85		20.15	0.781		0.793	
E	15.45		15.75	0.608		0.620	
е	5.30	5.45	5.60	0.209	0.215	0.220	
L	14.20		14.80	0.559		0.582	
L1	3.70		4.30	0.145		0.169	
L2		18.50			0.728		
ØP	3.55		3.65	0.139		0.143	
ØR	4.50		5.50	0.177		0.217	
S	5.30	5.50	5.70	0.209	0.216	0.224	

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3 Ordering information

Table 5. Order code

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPS61170CW	STPS61170CW	TO-247	4.36 g	30	Tube

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Revision history

Table 6. Document revision history

Date	Revision	Changes
16-Sep-2005	1	First issue.
01-Dec-2010	2	Updated Table 2 and added Figure 11.
27-Jul-2018	3	Updated Table 1. Absolute ratings (limiting values per diode at 25 $^{\circ}$ C, unless otherwise specified) and Figure 3. Normalized avalanche power derating versus pulse duration (T _j = 125 $^{\circ}$ C).

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